

Multiple-wave X-ray Diffraction at Resonance: An Iterative Born Approximation

**Wen-Hsien Sun (孫文賢), Yen-Sen Lin (林彥杉),
Shih-Chang Weng (翁世璋), and Shih-Ling Chang (張石麟)**

Department of Physics, Tsing Hua University, Hsinchu, Taiwan

The experiments were carried out at wiggler beamline, 17B, NSRRC and SP12B2 Spring 8. A [111]cut GaAs single crystal is used as a sample crystal. The diffracted intensity of three-beam(222)/(11 $\bar{3}$)case, as well as fluorescence yield was measured for the photon energies covering the Ga K and As K edges. Consider a three-wave (O, G, L) X-ray diffraction, in which O , G and L are incident, primary and secondary reflections, respectively. The fundamental equation can be expressed in terms of the electric displacement $\vec{D}$:

$$\left\{ \begin{array}{l} 2\mathcal{E}_0 D_0 = x_0 D_{0[0]} + x_{0-G} D_{G[0]} + x_{0-L} D_{L[0]} \\ 2\mathcal{E}_0 D_G = x_{G-0} D_{0[G]} + x_0 D_{G[G]} + x_{G-L} D_{L[G]} \\ 2\mathcal{E}_L D_L = x_{L-0} D_{0[L]} + x_{L-G} D_{G[L]} + x_0 D_{L[L]} \end{array} \right.$$

where

$$D_{H[i]H[j]} = -[\overrightarrow{K_{Hj}} \times (\overrightarrow{K_{Hj}} \times \overrightarrow{D_{Hi}})]$$

With a third-order Born approximation:

$$D_G^{(3)} \equiv A_G x_{G-O} D_G^{(2)} + A_G A_L \|x_{L-O}\| x_{G-L} |D_{O[L][G]}^{(2)}| - A_G A_O A_L \|x_{G-O}\| x_{L-O} |D_{O[L][O][G]}^{(2)}| - A_G^2 A_L \|x_{G-O}\| x_{L-G} \|x_{G-L}\| |D_{O[G][L][G]}^{(2)}|$$

Where the resonance term

$$A_H = \frac{1}{2\epsilon_0 - \chi_0}, \quad 2\epsilon_H = \frac{K_H^2 - k^2}{K_H^2} \quad (H \equiv O, G, L)$$

k is the magnitude of the incident wavevector in vacuum and K_H are the magnitudes of diffracted waves in the crystal. The three-wave intensity is then given by:

$$I_G^{(3)}(\psi_u) = I_G^{(2)} + I_D(\delta_3, \psi_u) + I_I(\psi_u) \quad (3)$$

$I_G^{(2)}$ is the two-wave intensity, $I_D(\delta_3, \psi_u)$ is the phase dependent part of the three-wave intensity and $I_l(\psi_u)$ is its phase independent part. Experimentally, the fluorescence yield and multiple-wave diffraction intensities as a function of the Bragg angle and azimuth angle of rotation of a symmetric Bragg primary reflection were measured. The asymmetric intensity ratio R_v of three-wave diffraction is defined as $R_v = (I_2 - I_{\min}) / (I_{\max} - I_2)$, where $I_{\max}$ and $I_{\min}$ are the maximum and minimum intensities of three-wave diffraction measured. R_v is used for both theoretical and experimental analysis. The real part f' and imaginary f'' of dispersion corrections on the atomic scattering factors versus the photon energy are deduced then from R_v (See Fig.1), where f' can be obtained via 2-dimension interpolating surface splines. Finally, the fine structure function χ can be determined from f' and f'' . The experimental and theoretical χ 's are shown in Fig. 2.

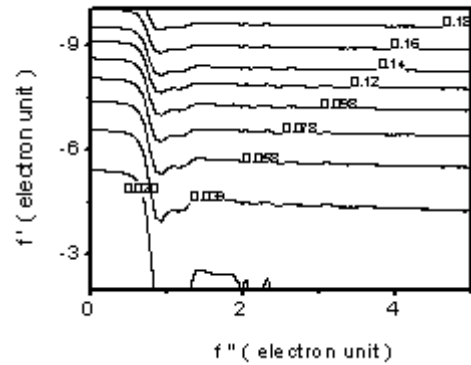


Figure 1. 3-Dimension distribution of theoretical Rv

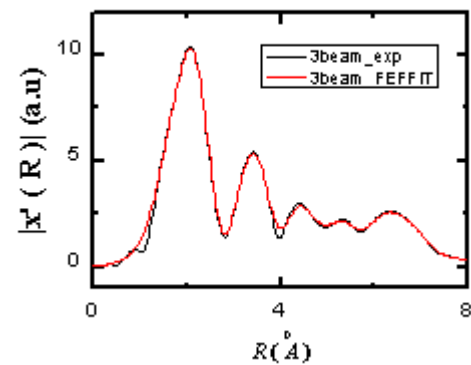


Figure 2. The structure function x .